

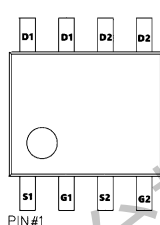
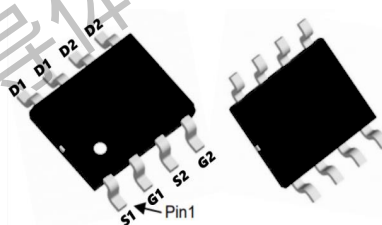
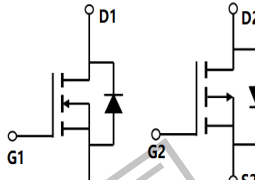
TM4606S

N+P-Channel Enhancement Mode Mosfet

General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features N Channel $V_{DS} = 30V$ $I_D = 8.6A$ $R_{DS(ON)} = 16.7m\Omega (typ) @ V_{GS} = 10V$ P Channel $V_{DS} = -30V$ $I_D = -7.5A$ $R_{DS(ON)} = 32m\Omega (typ) @ V_{GS} = -10V$ 100% UIS Tested 100% R_g Tested
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S: SOP-8L

Marking: 4606A OR 4606

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	8.6	-7.5	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	6.2	-5.5	A
I_{DM}	Pulsed Drain Current	21.5	-18.7	A
EAS	Single Pulse Avalanche Energy	12	43	mJ
I_{AS}	Avalanche Current	9	17	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation	2	2	W
T_{STG}	Storage Temperature Range	-55 to 175	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	62.5	$^\circ C/W$

TM4606S

N+P-Channel Enhancement Mode Mosfet

N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.2	1.6	2.0	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	64			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=7.2\text{A}$		16.7	20	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=5\text{A}$		22	36	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=7.2\text{A}$		20		S
V_{SD}	Diode Forward Voltage	$I_S=2.5\text{A}$, $V_{GS}=0\text{V}$		0.74	1	V
I_S	Maximum Body-Diode Continuous Current				8.6	A
I_{SM}	Pulsed Body-Diode Current ^B				64	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		373	448	pF
C_{oss}	Output Capacitance			67		pF
C_{rss}	Reverse Transfer Capacitance			41		pF
R_g (Note.H)	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.8	2.8	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=7.2\text{A}$		7.2	11	nC
$Q_g(4.5\text{V})$	Total Gate Charge			3.5		nC
Q_{gs}	Gate Source Charge			1.3		nC
Q_{gd}	Gate Drain Charge			1.7		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=2.1\Omega$, $R_{GEN}=3\Omega$		4.5		ns
t_r	Turn-On Rise Time			2.7		ns
$t_{D(off)}$	Turn-Off DelayTime			14.9		ns
t_f	Turn-Off Fall Time			2.9		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=7.2\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		10.5	12.6	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=7.2\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		4.5		nC

TM4606S

N+P-Channel Enhancement Mode Mosfet

N-Channel Typical Characteristics

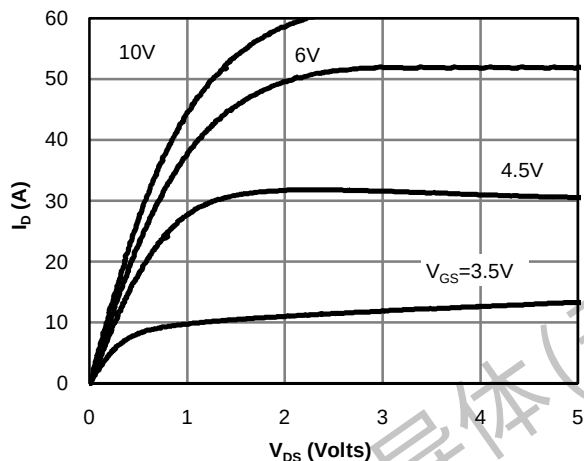


Fig 1: On-Region Characteristics

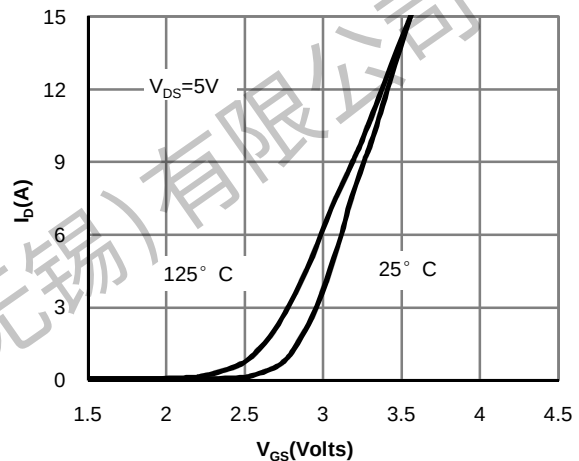


Figure 2: Transfer Characteristics

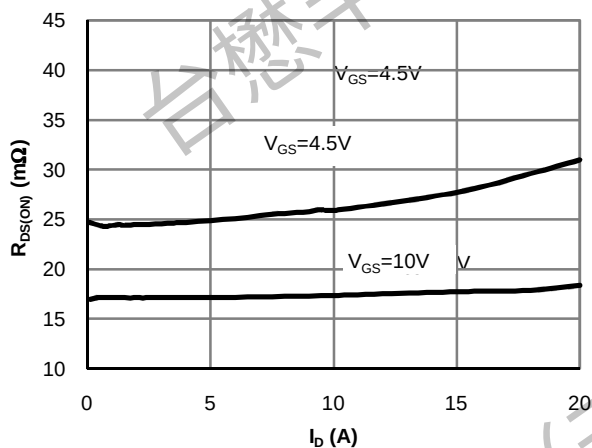


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

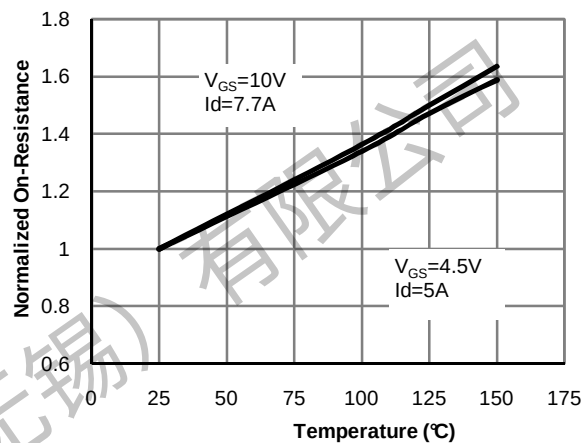


Figure 4: On-Resistance vs. Junction Temperature

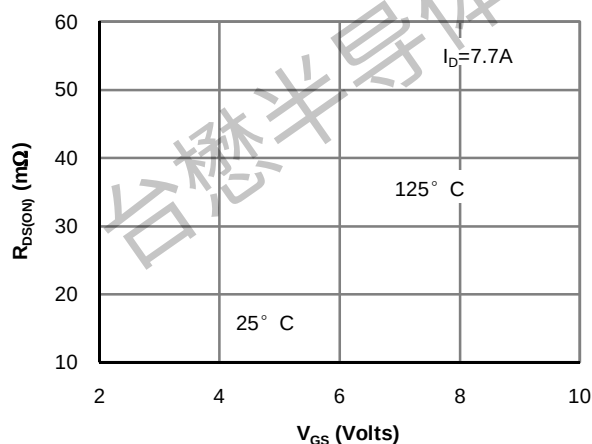


Figure 5: On-Resistance vs. Gate-Source Voltage

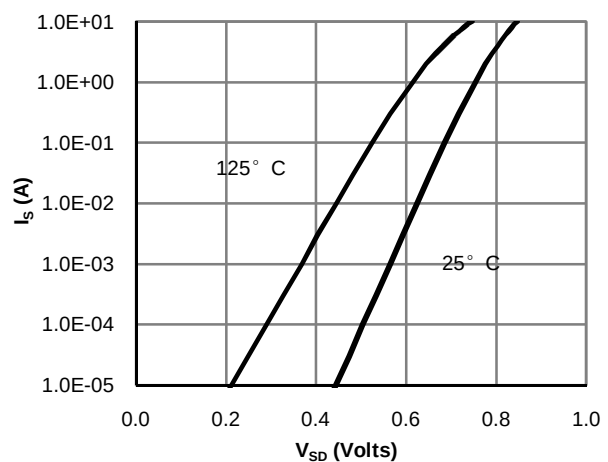


Figure 6: Body-Diode Characteristics

TM4606S

N+P-Channel Enhancement Mode Mosfet

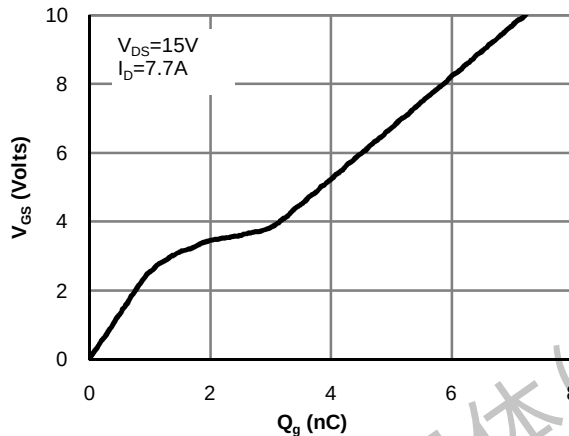


Figure 7: Gate-Charge Characteristics

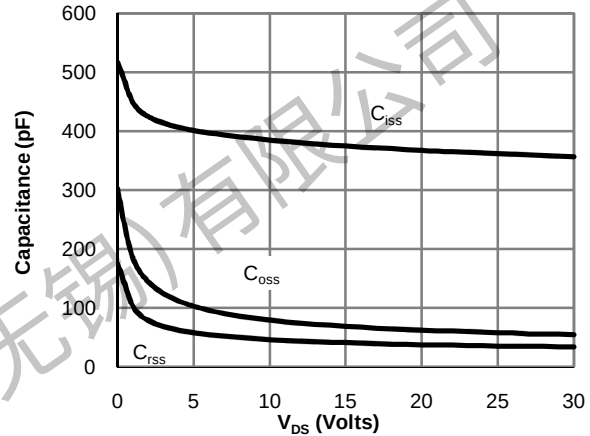


Figure 8: Capacitance Characteristics

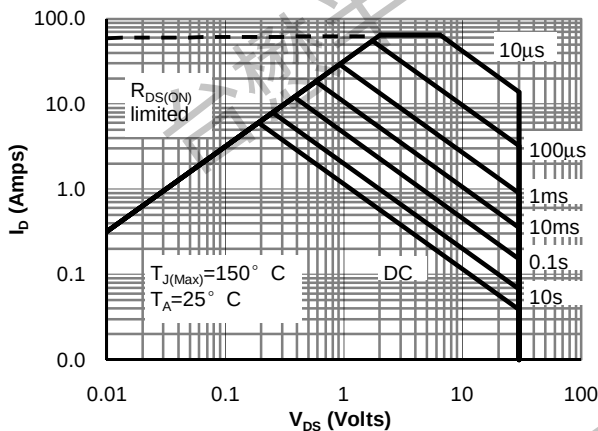


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

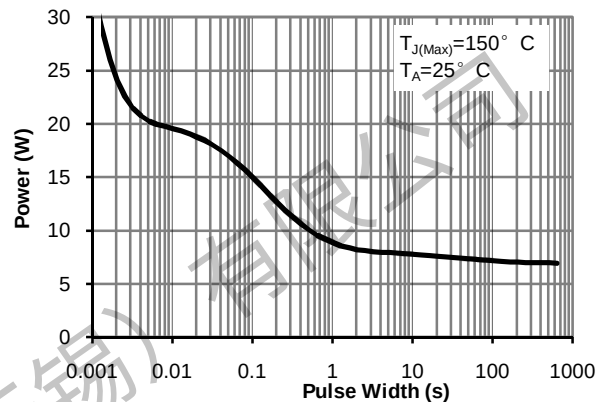


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

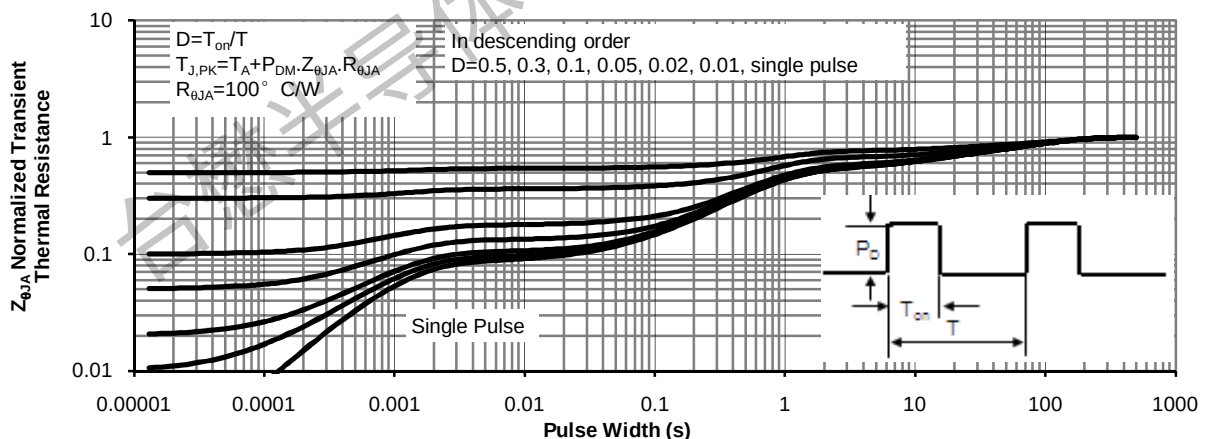


Figure 11: Normalized Maximum Transient Thermal Impedance

TM4606S

N+P-Channel Enhancement Mode Mosfet

P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.0	-1.5	-2.0	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	-40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-6.3\text{A}$		32	38	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-4.5\text{A}$		39	49	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-5.3\text{A}$		19		S
V_{SD}	Diode Forward Voltage	$I_S=-3.5\text{A}$, $V_{GS}=0\text{V}$		-0.8	-1	V
I_S	Maximum Body-Diode Continuous Current				-7.5	A
I_{SM}	Pulsed Body-Diode Current ^B				-40	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		760		pF
C_{oss}	Output Capacitance			140		pF
C_{rss}	Reverse Transfer Capacitance			95		pF
R_g (Note.H)	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3.2	5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-5.3\text{A}$		13.6	16	nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			6.7		nC
Q_{gs}	Gate Source Charge			2.5		nC
Q_{gd}	Gate Drain Charge			3.2		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=2.8\Omega$, $R_{GEN}=3\Omega$		8		ns
t_r	Turn-On Rise Time			6		ns
$t_{D(off)}$	Turn-Off DelayTime			17		ns
t_f	Turn-Off Fall Time			5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-5.3\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		15		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-5.3\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		9.7		nC

TM4606S

N+P-Channel Enhancement Mode Mosfet

P-Typical Characteristics

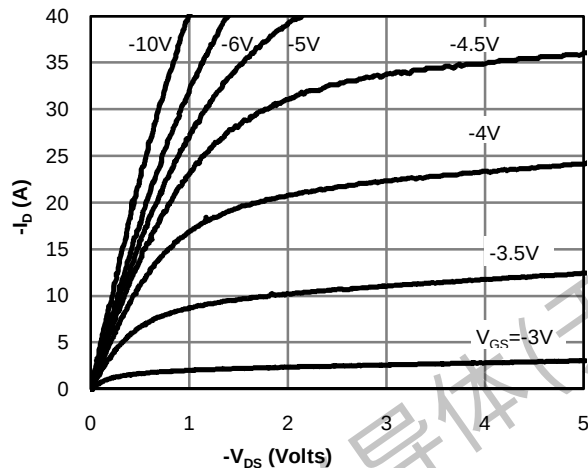


Fig 1: On-Region Characteristics

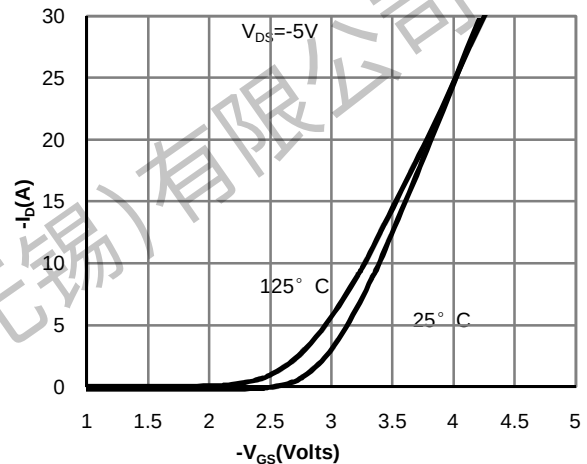


Figure 2: Transfer Characteristics

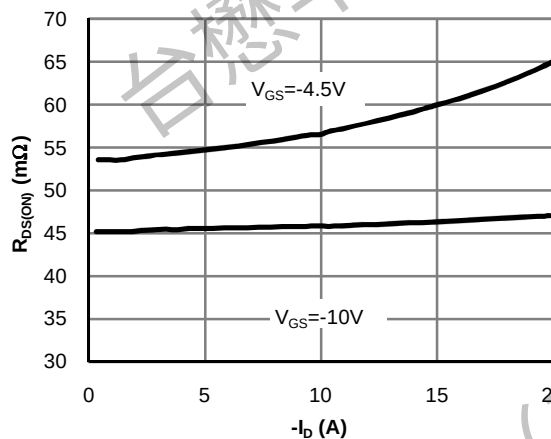


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

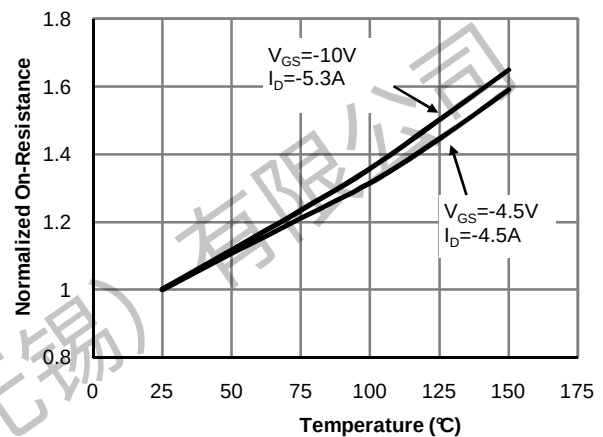


Figure 4: On-Resistance vs. Junction Temperature

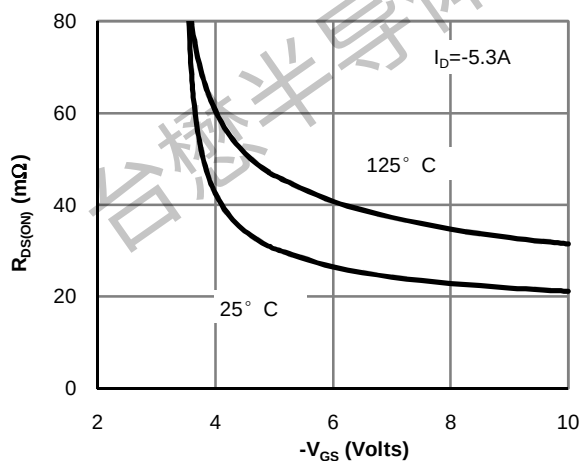


Figure 5: On-Resistance vs. Gate-Source Voltage

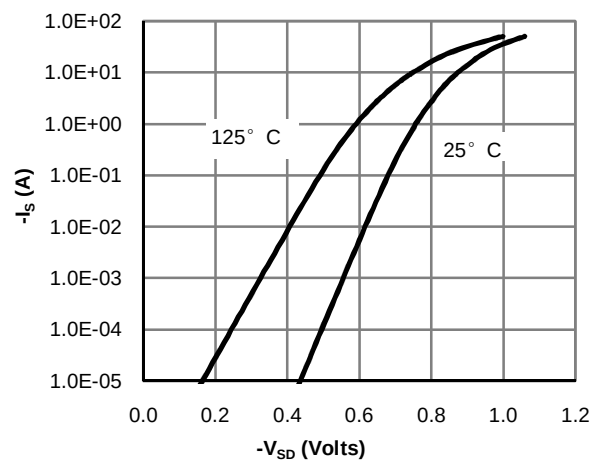
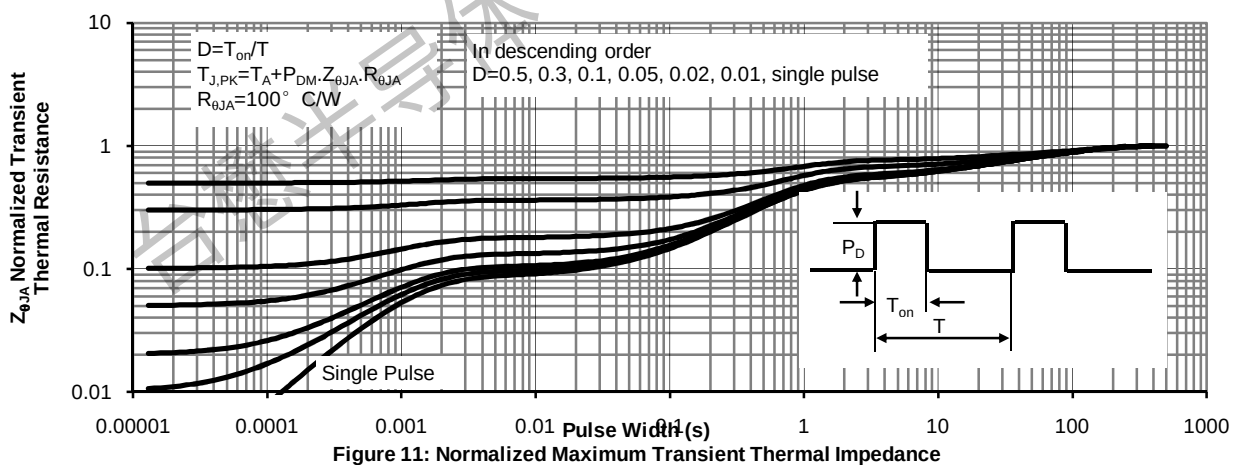
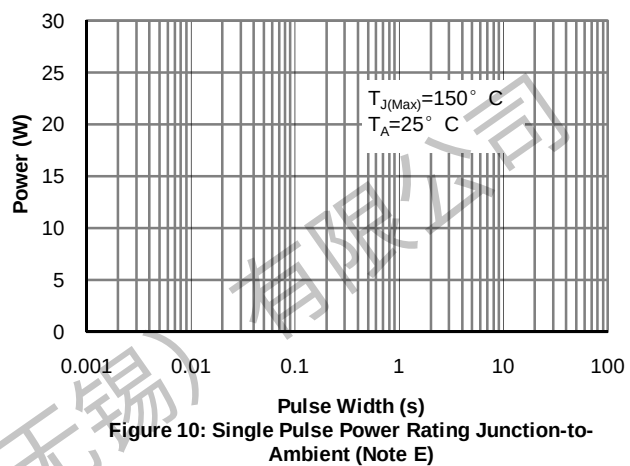
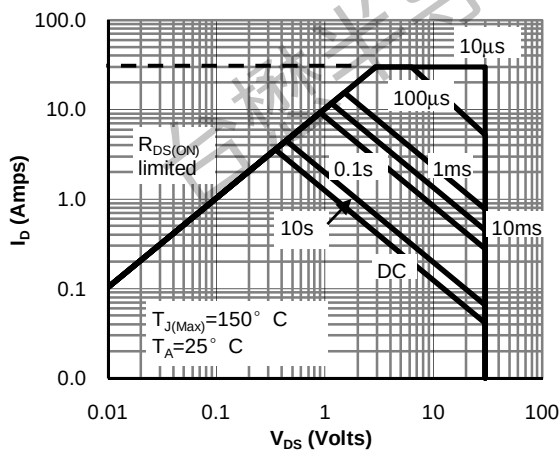
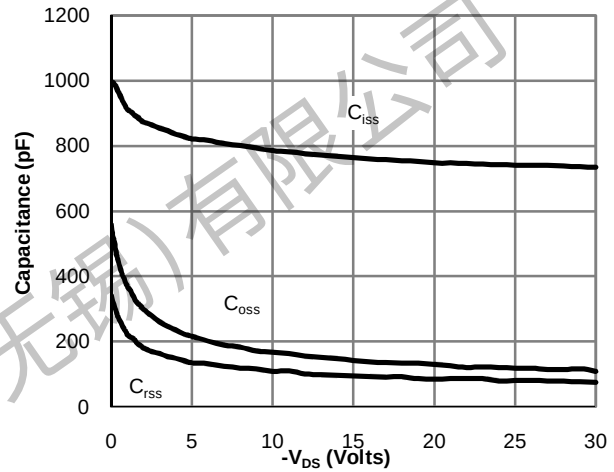
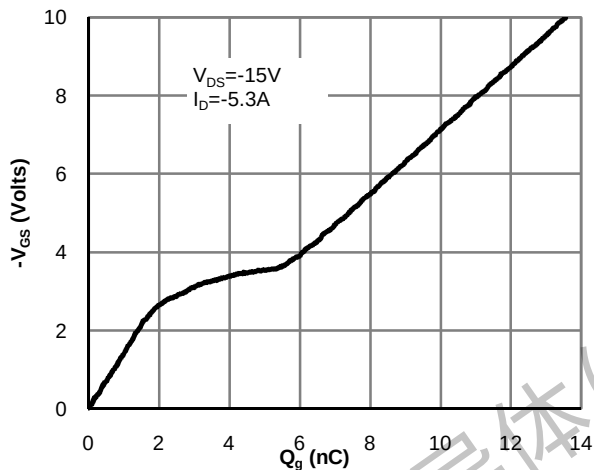


Figure 6: Body-Diode Characteristics

TM4606S

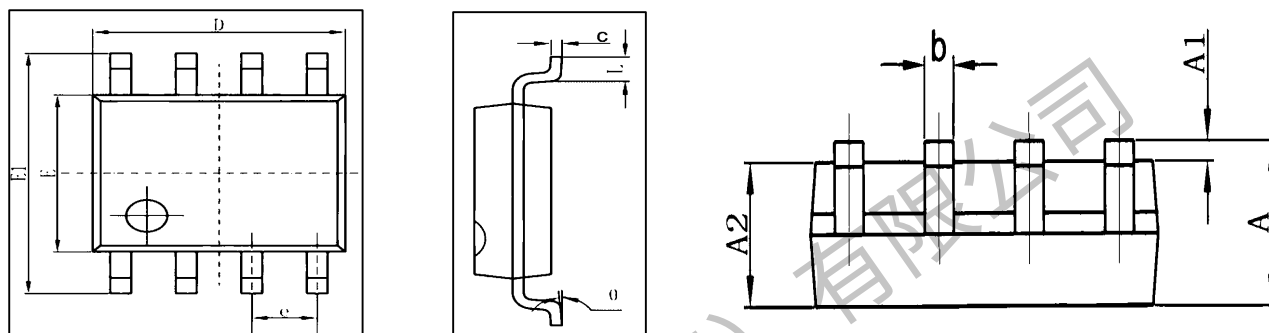
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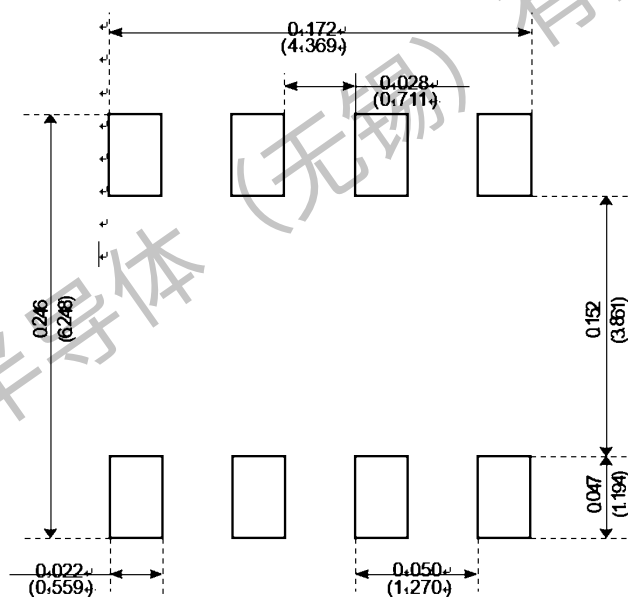
TM4606S

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Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

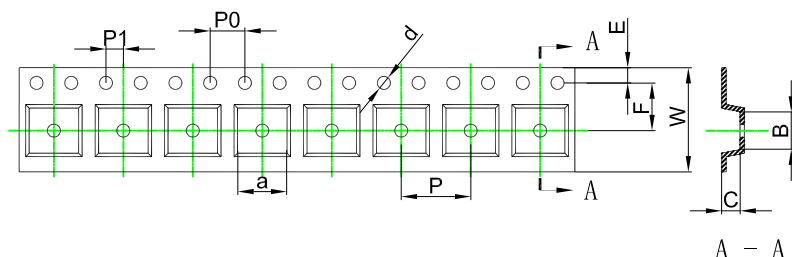


Recommended Minimum Pads

TM4606S

N+P-Channel Enhancement Mode Mosfet

SOP-8L Embossed Carrier Tape



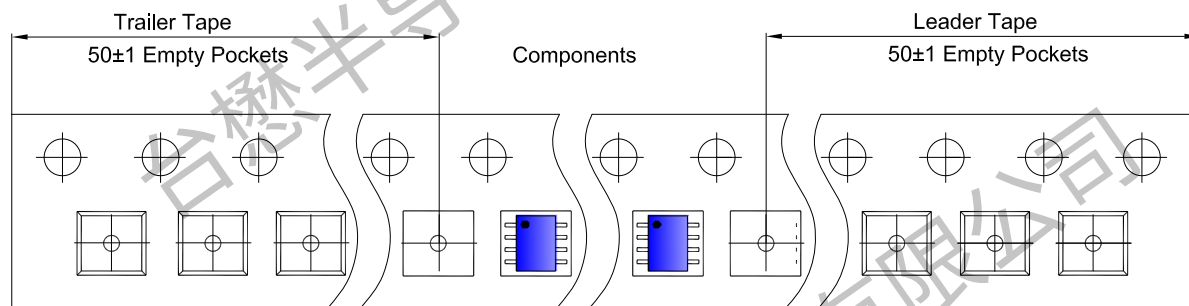
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

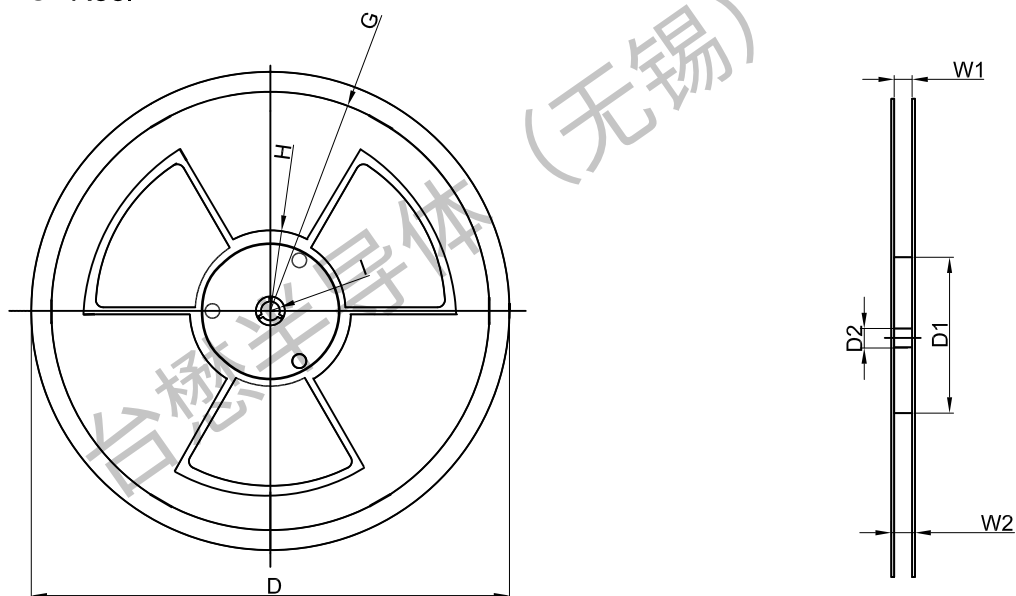
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOP-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

SOP-8L Tape Leader and Trailer



SOP-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3,000 pcs	13 inch	6,000 pcs	370×355×52	48,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2024.06.04	24.06	Original	